

**IRF840****N-CHANNEL 500V - 0.75Ω - 8A TO-220****PowerMesh™II MOSFET**

TYPE	V _{DSS}	R _{DS(on)}	I _D
IRF840	500 V	< 0.85 Ω	8 A

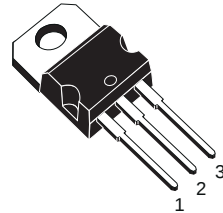
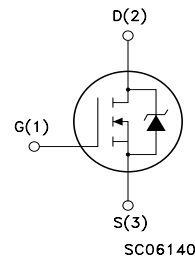
- TYPICAL R_{DS(on)} = 0.75 Ω
- EXTREMELY HIGH dv/dt CAPABILITY
- 100% AVALANCHE TESTED
- NEW HIGH VOLTAGE BENCHMARK
- GATE CHARGE MINIMIZED

DESCRIPTION

The PowerMESH™II is the evolution of the first generation of MESH OVERLAY™. The layout refinements introduced greatly improve the Ron*area figure of merit while keeping the device at the leading edge for what concerns switching speed, gate charge and ruggedness.

APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SWITCH MODE POWER SUPPLIES (SMPS)
- DC-AC CONVERTERS FOR WELDING EQUIPMENT AND UNINTERRUPTIBLE POWER SUPPLIES AND MOTOR DRIVES

**TO-220****INTERNAL SCHEMATIC DIAGRAM****ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
V _{DS}	Drain-source Voltage (V _{GS} = 0)	500	V
V _{DGR}	Drain-gate Voltage (R _{GS} = 20 kΩ)	500	V
V _{GS}	Gate- source Voltage	± 20	V
I _D	Drain Current (continuous) at T _C = 25°C	8	A
I _D	Drain Current (continuous) at T _C = 100°C	5.1	A
I _{DM} (•)	Drain Current (pulsed)	32	A
P _{TOT}	Total Dissipation at T _C = 25°C	125	W
	Derating Factor	1.0	W/°C
dv/dt (1)	Peak Diode Recovery voltage slope	3.5	V/ns
T _{stg}	Storage Temperature	–65 to 150	°C
T _j	Max. Operating Junction Temperature	150	°C

(•)Pulse width limited by safe operating area

(1)I_{SD} ≤ 8A, di/dt ≤ 50A/μs, V_{DD} ≤ V_{(BR)DSS}, T_j ≤ T_{JMAX}.

THERMAL DATA

R _{thj-case}	Thermal Resistance Junction-case Max	1	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient Max	62.5	°C/W
T _l	Maximum Lead Temperature For Soldering Purpose	300	°C

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I _{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T _j max)	8	A
E _{AS}	Single Pulse Avalanche Energy (starting T _j = 25 °C, I _D = I _{AR} , V _{DD} = 50 V)	520	mJ

ELECTRICAL CHARACTERISTICS (T_{CASE} = 25 °C UNLESS OTHERWISE SPECIFIED)
OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown Voltage	I _D = 250 μA, V _{GS} = 0	500			V
I _{DSS}	Zero Gate Voltage Drain Current (V _{GS} = 0)	V _{DS} = Max Rating V _{DS} = Max Rating, T _C = 125 °C			1 50	μA μA
I _{GSS}	Gate-body Leakage Current (V _{DS} = 0)	V _{GS} = ± 20V			±100	nA

ON (1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	2	3	4	V
R _{DS(on)}	Static Drain-source On Resistance	V _{GS} = 10V, I _D = 3.5 A		0.75	0.85	Ω

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g _{fs} (1)	Forward Transconductance	V _{DS} > I _{D(on)} × R _{DS(on)max} , I _D = 3.5A		6.4		S
C _{iss}	Input Capacitance	V _{DS} = 25V, f = 1 MHz, V _{GS} = 0		832		pF
C _{oss}	Output Capacitance			131		pF
C _{rss}	Reverse Transfer Capacitance			17		pF

ELECTRICAL CHARACTERISTICS (CONTINUED)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Delay Time Rise Time	$V_{DD} = 250\text{ V}$, $I_D = 3.5\text{ A}$ $R_G = 4.7\Omega$, $V_{GS} = 10\text{ V}$ (see test circuit, Figure 3)		10 21		ns ns
Q_g	Total Gate Charge	$V_{DD} = 400\text{ V}$, $I_D = 7\text{ A}$, $V_{GS} = 10\text{ V}$		29.6	39	nC
Q_{gs}	Gate-Source Charge			4.9		nC
Q_{gd}	Gate-Drain Charge			13.9		nC

SWITCHING OFF

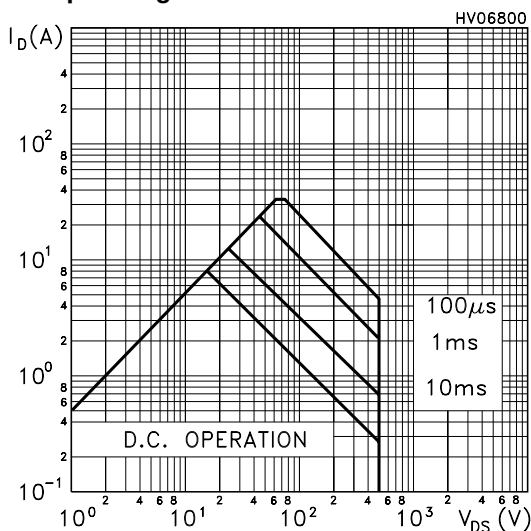
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_r(V_{off})$	Off-voltage Rise Time	$V_{DD} = 400\text{ V}$, $I_D = 7\text{ A}$, $R_G = 4.7\Omega$, $V_{GS} = 10\text{ V}$ (see test circuit, Figure 5)		9		ns
t_f	Fall Time			9		ns
t_c	Cross-over Time			19		ns

SOURCE DRAIN DIODE

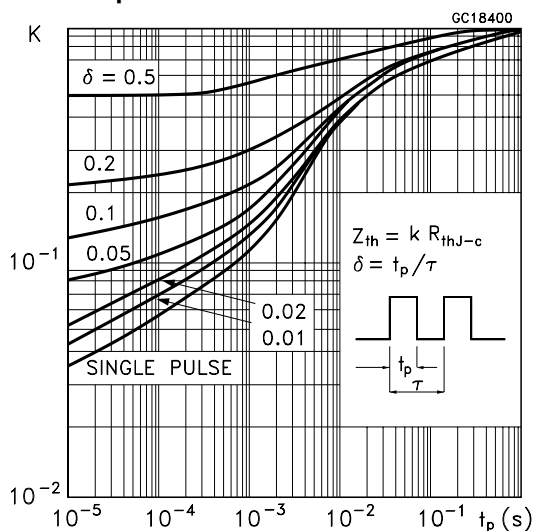
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				8	A
$I_{SDM}(2)$	Source-drain Current (pulsed)				32	A
$V_{SD}(1)$	Forward On Voltage	$I_{SD} = 8\text{ A}$, $V_{GS} = 0$			1.6	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 7\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 100\text{ V}$, $T_J = 150^\circ\text{C}$ (see test circuit, Figure 5)		384		ns
Q_{rr}	Reverse Recovery Charge			2.2		μC
I_{RRM}	Reverse Recovery Current			11.8		A

Note: 1. Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.
2. Pulse width limited by safe operating area.

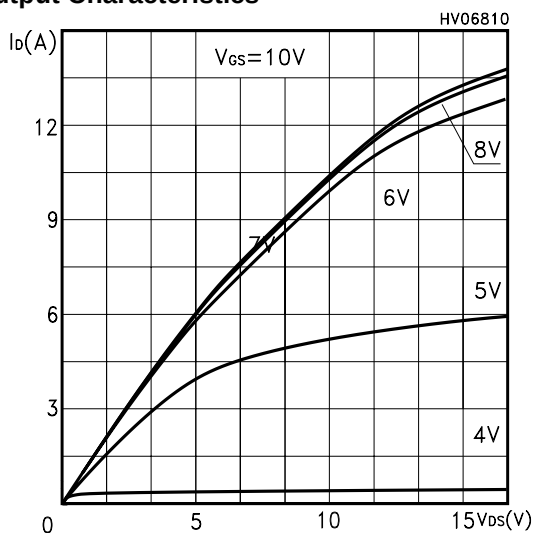
Safe Operating Area



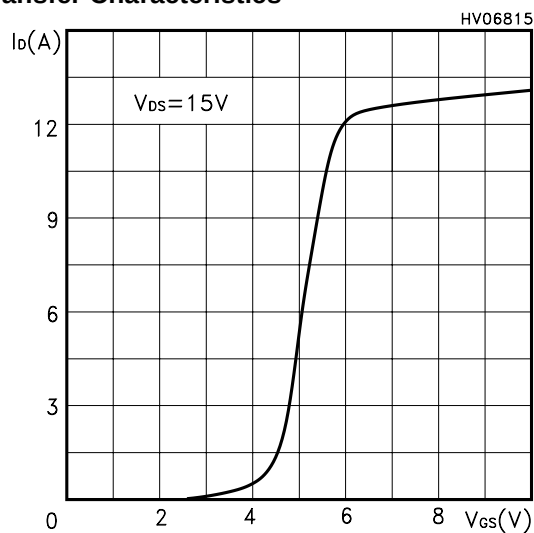
Thermal Impedance



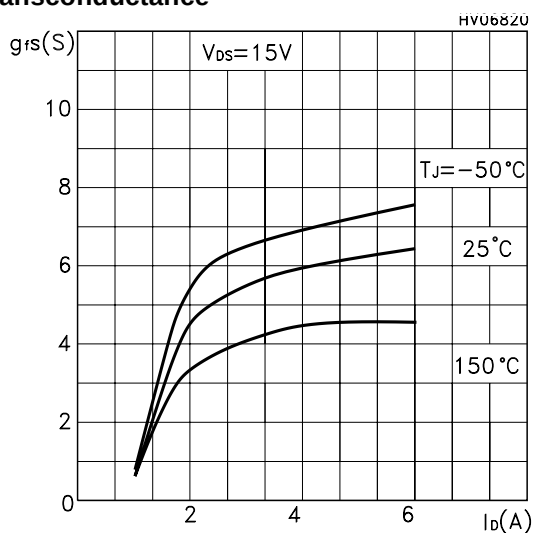
Output Characteristics



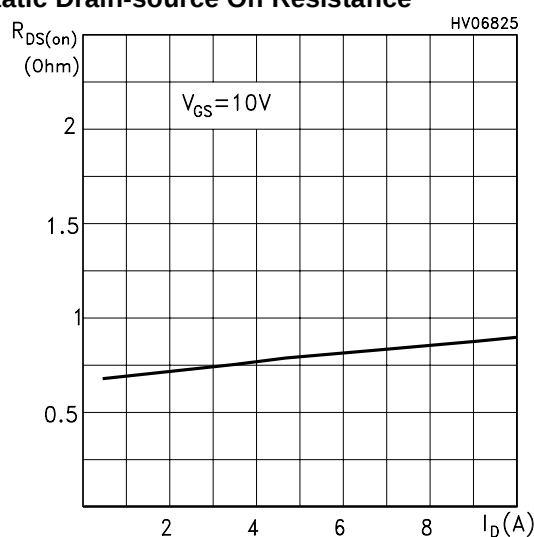
Transfer Characteristics



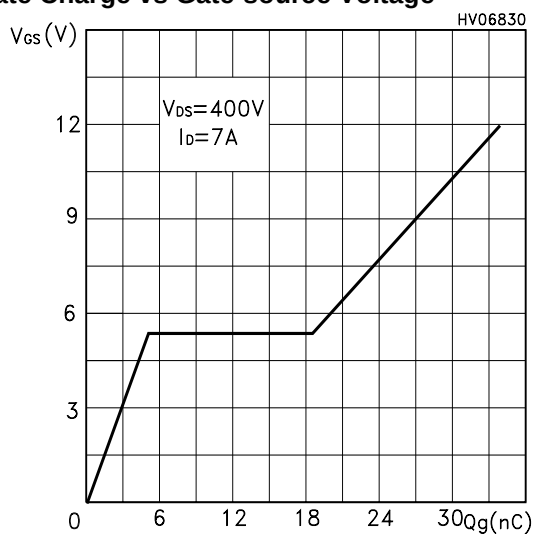
Transconductance



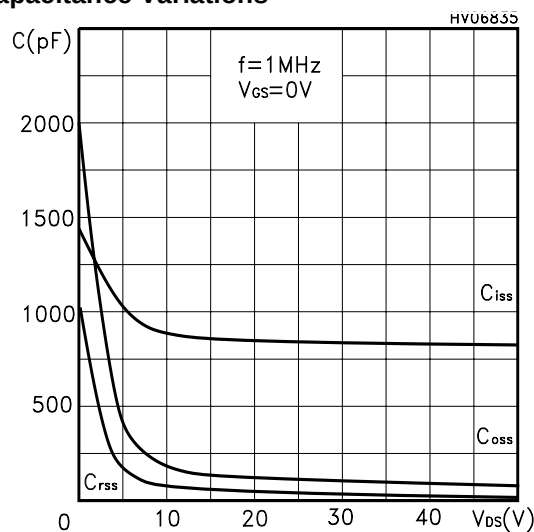
Static Drain-source On Resistance



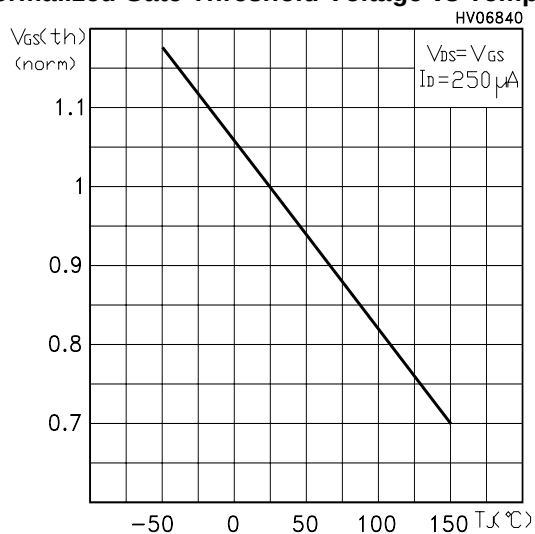
Gate Charge vs Gate-source Voltage



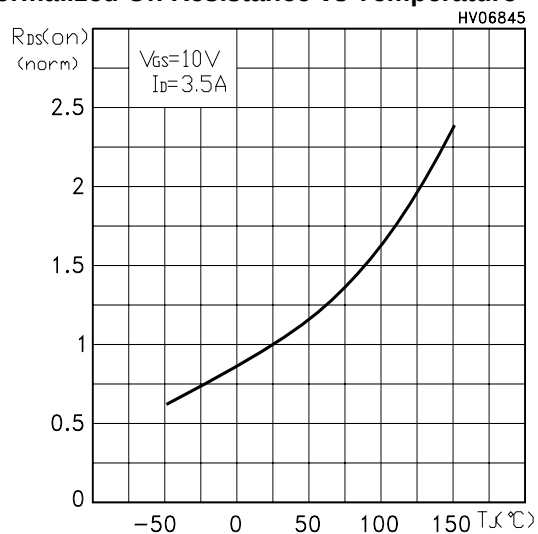
Capacitance Variations



Normalized Gate Threshold Voltage vs Temp.



Normalized On Resistance vs Temperature



Source-drain Diode Forward Characteristics

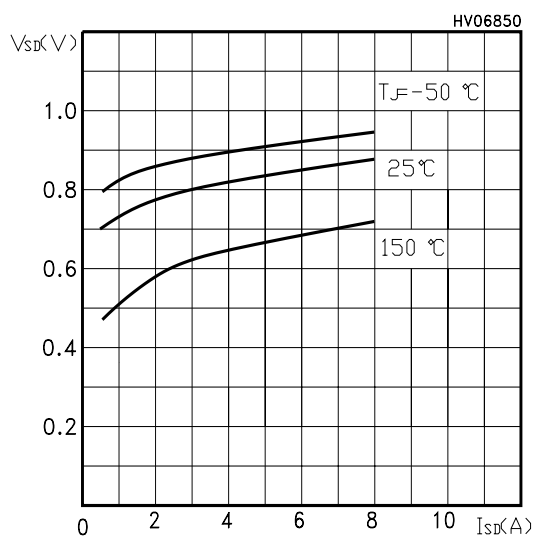


Fig. 1: Unclamped Inductive Load Test Circuit

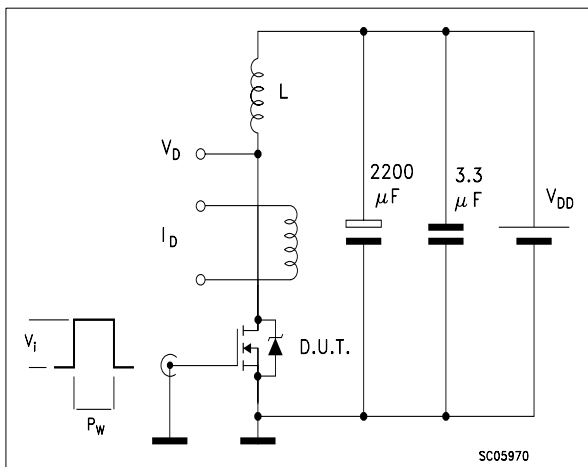


Fig. 2: Unclamped Inductive Waveform

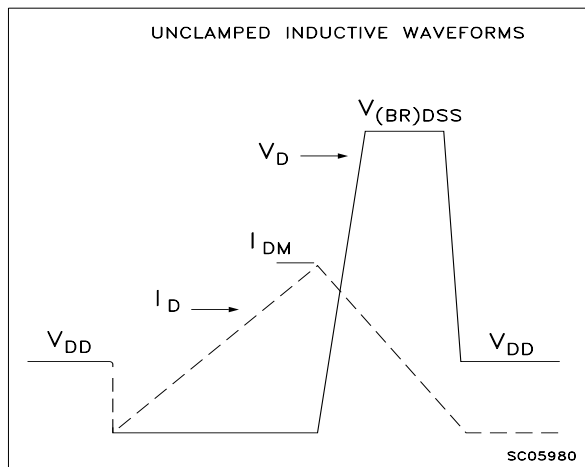


Fig. 3: Switching Times Test Circuit For Resistive Load

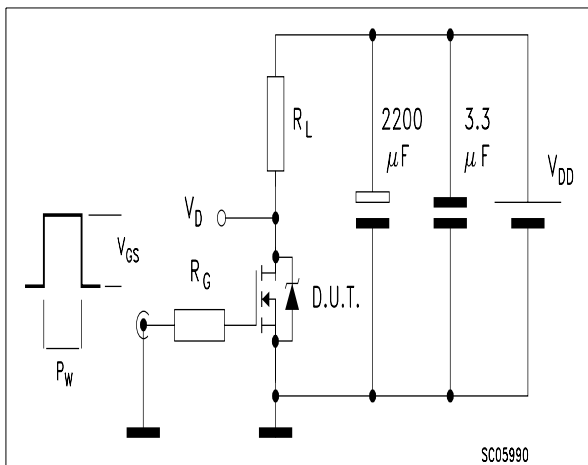


Fig. 4: Gate Charge test Circuit

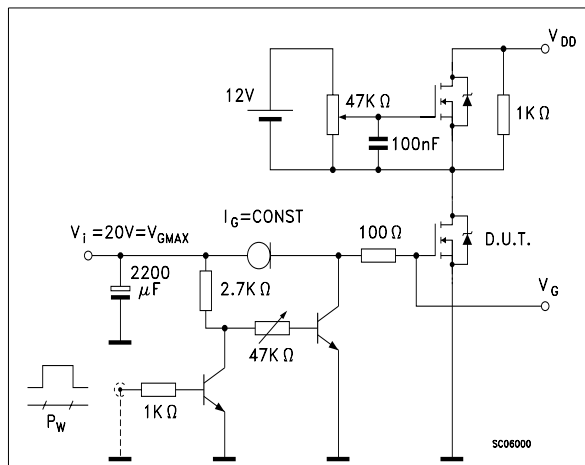
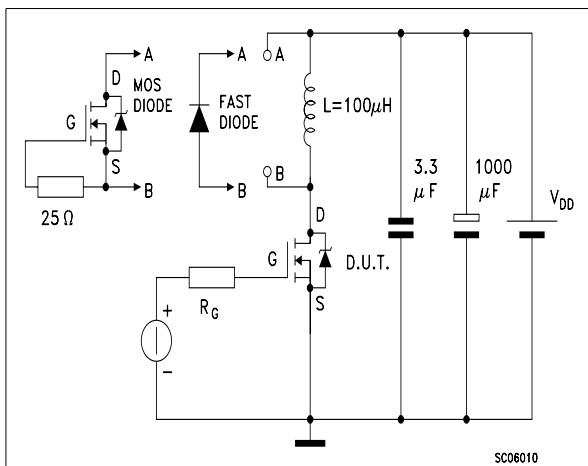
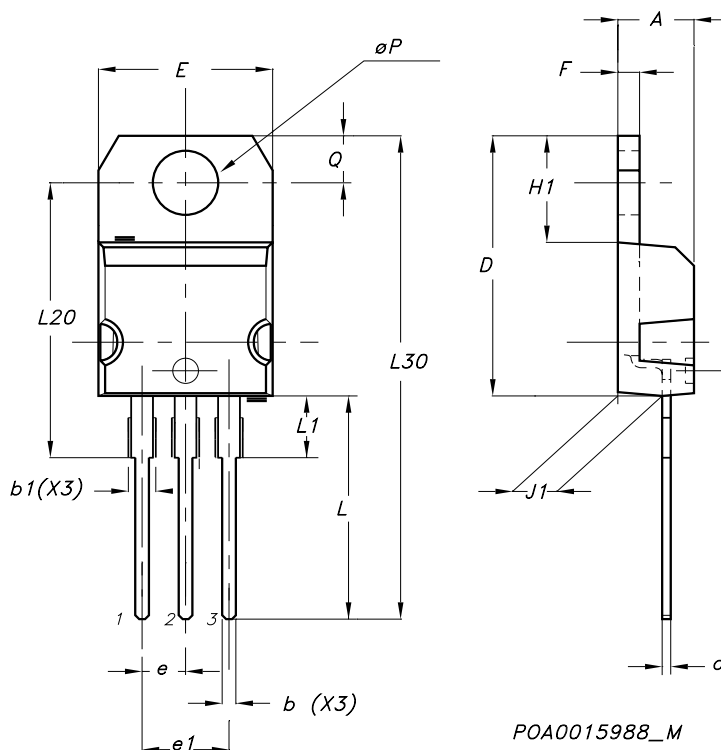


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



TO-220 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.15		1.70	0.045		0.066
c	0.49		0.70	0.019		0.027
D	15.25		15.75	0.60		0.620
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.052
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
øP	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



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